



JT05N065RAD/VAD/SAD

主要参数 MAIN CHARACTERISTICS

I _c	5 A
V _{CES}	650V
V _{cesat-typ} (V _{ge} =15V)	1.7V

用途

- 逆变器
- PDP
- UPS 电源

APPLICATIONS

- General purpose inverters
- PDP
- UPS

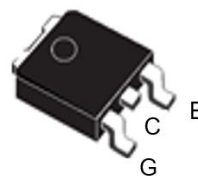
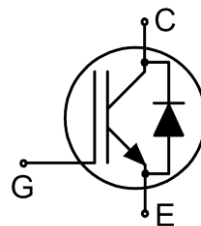
产品特性

- 低栅极电荷
- FS 技术
- 通态压降
- RoHS 产品

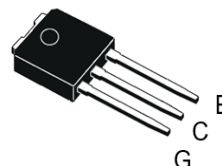
FEATURES

- Low gate charge
- FS Technology
- saturation voltage
- RoHS product

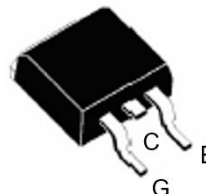
封装 Package



DPAK



IPAK



TO-263

订货信息 ORDER MESSAGE

订货型号 Order codes		印记 Marking	封装 Package
无卤-条管 Non halogen-Tube	无卤-编带 Non halogen-Reel		
JT05N065RAD-R-BR	JT05N065RAD-R-AR	JT05N065RAD	DPAK
JT05N065VAD-V-BR	N/A	JT05N065VAD	IPAK
JT05N065SAD-S-BR	JT05N065SAD-S-AR	JT05N065SAD	TO-263





绝对最大额定值 ABSOLUTE RATINGS (Tc=25℃)

项 目 Parameter	符 号 Symbol	数 值 Value		单 位 Unit
		JT05N065RAD/VAD	JT05N065SAD	
最高集电极—发射极直流电压 Collector-Emitter Voltage	V _{ce}	650	650	V
*连续集电极电流 Collector Current-continuous	I _c T=25℃ T=100℃	10	10	A
		5	5	A
最大脉冲集电极极电流（注1） Collector Current – pulse (note 1)	I _{CM}	20	20	A
最高栅极发射极电压 Gate-Emitter Voltage	V _{GE}	±30	±30	V
安全工作区电流 Turn-off safe area	-	20	20	A
耗散功率 Power Dissipation	P _D T _C =25℃	59.5	96	W
最高结温及存储温度 Operating and Storage Temperature Range	T _{VJ} , T _{STG}	-55~+150	-55~+150	℃
引线最高焊接温度 Maximum Lead Temperature for Soldering Purposes	T _L	300	300	℃

*连续集电极电流由最高结温限制

*Collector current limited by maximum junction temperature





电特性 ELECTRICAL CHARACTERISTICS

项 目 Parameter	符 号 Symbol	测试条件 Tests conditions	最小 Min	典型 Typ	最大 Max	单 位 Units
关态特性 Off –Characteristics						
集电极-发射极击穿电压 Collector-Emitter Voltage	BV_{CES}	$I_C=250\mu A, V_{GE}=0V$	650	-	-	V
击穿电压温度特性 Breakdown Voltage Temperature Coefficient	$\Delta BV_{CES}/\Delta T_J$	$I_C=1mA$, referenced to $25^\circ C$	-	0.5	-	$V/^\circ C$
零栅压下集电极漏电流 Zero Gate Voltage Collector Current	I_{CES}	$V_{CE}=650V, V_{GE}=0V, T_C=25^\circ C$	-	-	10	μA
正向栅极体漏电流 Gate-body leakage current, forward	I_{GESF}	$V_{CE}=0V, V_{GE}=20V$	-	-	200	nA
反向栅极体漏电流 Gate-body leakage current, reverse	I_{GESR}	$V_{CE}=0V, V_{GE}=-20V$	-	-	-200	nA
通态特性 On-Characteristics						
阈值电压 Gate Threshold Voltage	$V_{GE(th)}$	$V_{CE} = V_{GE}, I_C=250\mu A$	4.5	-	6.5	V
饱和压降 Collector-Emitter saturation Voltage	V_{CESAT}	$V_{GE}=15V, I_C=5A, T_J=25^\circ C$	-	1.7	2.05	V
动态特性 Dynamic Characteristics						
输入电容 Input capacitance	C_{ies}	$V_{CE}=25V, V_{GE}=0V, f=1.0MHz, T_J=25^\circ C$	-	289	-	pF
输出电容 Output capacitance	C_{oes}		-	32.7	-	pF
反向传输电容 Reverse transfer capacitance	C_{res}		-	7.4	-	pF
栅极电荷总量-Total Gate Charge	Q_g	$V_{CC}=400V, I_C=5A, R_G=10\Omega, V_{GE}=15V, T_J=25^\circ C$	-	11.8	-	nC
栅极-发射极电荷 Gate to Emitter charge	Q_{ge}		-	2.57	-	
栅极-集电极电荷 Gate to collector charge	Q_{gc}		-	5.1	-	
栅极电阻 Gate resistance	R_g	$f=1MHz$, open collector	-	1.6	-	Ω
短路电流- Short current	I_{sc}	$V_{GE}=15V, V_{CE}=400V, T_{Jstart} \leq 150^\circ C, t_{sc} \leq 10\mu s$	-	30	-	A





电特性 ELECTRICAL CHARACTERISTICS

开关特性 Switching Characteristics						
项 目 Parameter	符 号 Symbol	测试条件 Tests conditions	最小 Min	典型 Typ	最大 Max	单 位 Units
开启延迟时间 Turn-on delay time	$t_{d(on)}$	$V_{CC}=400V, I_c=5A, R_G=60\Omega$ $V_{GE}=15V$ $T_j=25^\circ C$	-	22	-	ns
上升时间 Turn-on rise time	t_r		-	13	-	ns
关断延迟时间 Turn-off delay time	$t_{d(off)}$		-	91	-	ns
下降时间 Turn-off Fall time	t_f		-	25	-	ns
开通损耗 Turn-on energy	E_{on}		-	123	-	μJ
关断损耗 Turn-off energy	E_{off}		-	53	-	μJ
总开关损耗 Total switching energy	E_{tot}		-	176	-	μJ
反并联二极管特性及最大额定值 Anti-Parallel Diode Characteristics and Maximum Ratings						
正向压降 Diode Forward Voltage	V_F	$V_{GE}=0V, I_F=5A, T_j=25^\circ C$	-	1.5	2.2	V
反向恢复时间 Diode Reverse recovery time	t_{rr}	$V_{GE}=0V, V_R=400V, I_F=5A$ $di_F/dt=200A/\mu s, T_j=25^\circ C$	-	33	-	ns
反向恢复电荷 Diode Reverse recovery charge	Q_{rr}		-	145	-	nC
反向恢复电流 Diode Reverse recovery Current	I_{RRM}		-	2.7	-	A

项 目 Parameter	符 号 Symbol	最大值 Max		单 位 Unit
		JT05N065RAD/VAD	JT05N065SAD	
结到管壳的热阻-IGBT Thermal Resistance, Junction to Case	$R_{th(j-c)}$	2.1	1.3	$^\circ C/W$
结到环境的热阻 Thermal Resistance, Junction to Ambient	$R_{th(j-A)}$	110	60	$^\circ C/W$

注释:

1: 脉冲宽度由最高结温限制

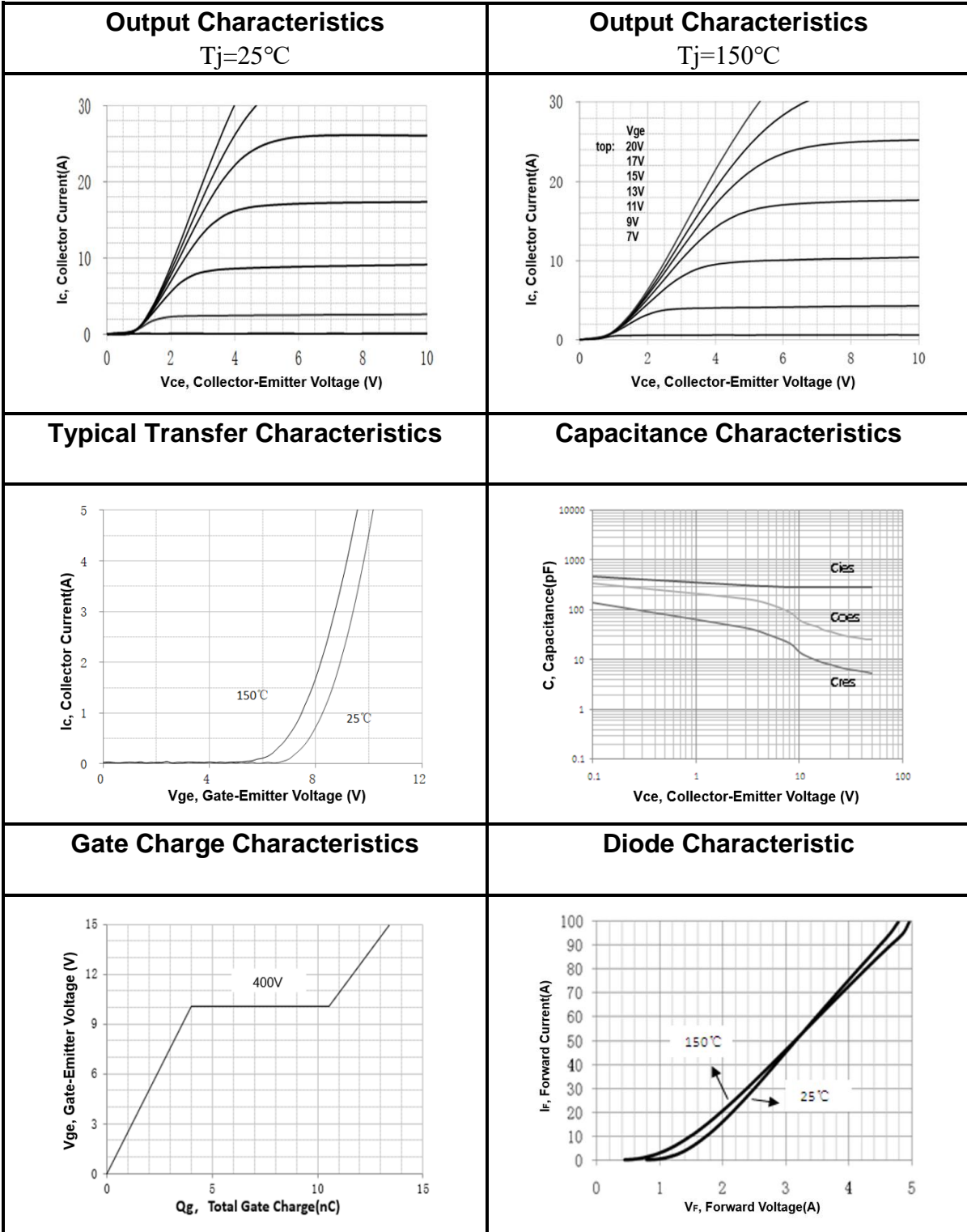
Notes:

1: Pulse width limited by maximum junction temperature



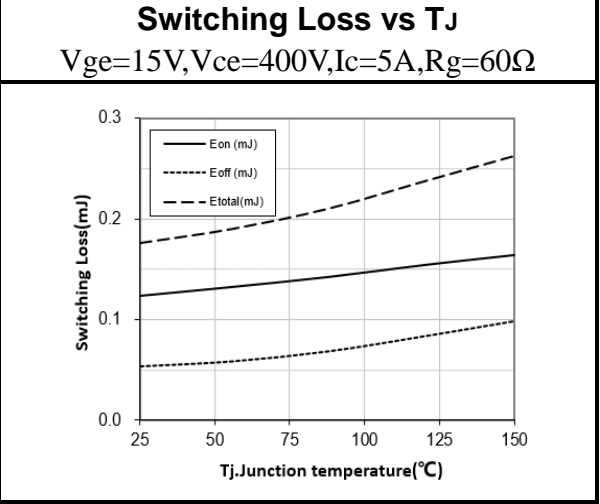
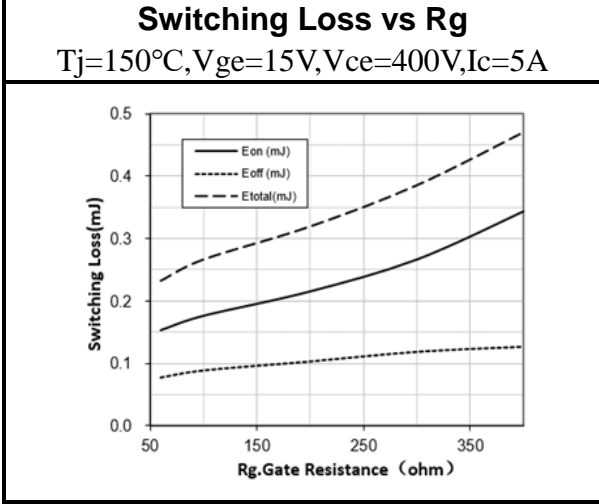
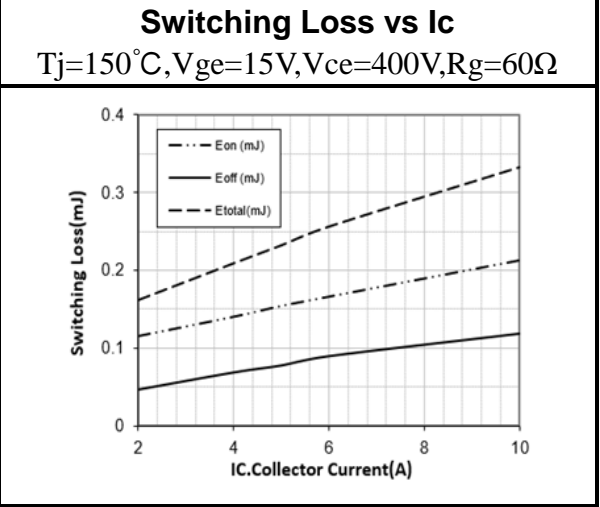
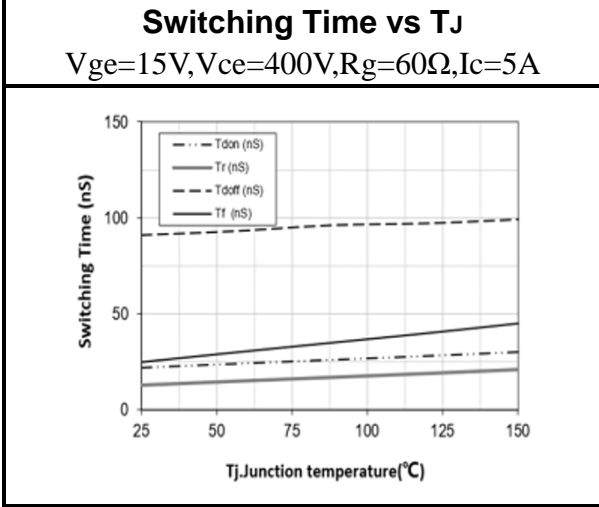
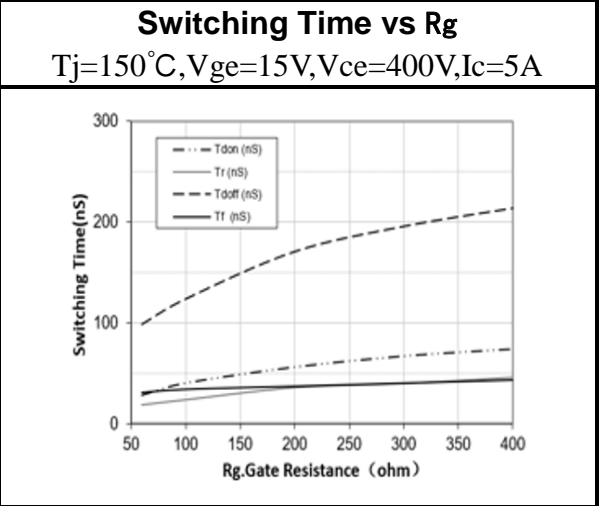
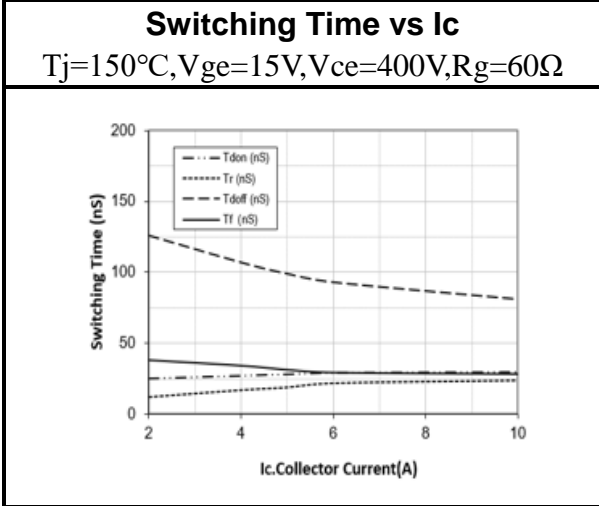


特征曲线 ELECTRICAL CHARACTERISTICS (curves)



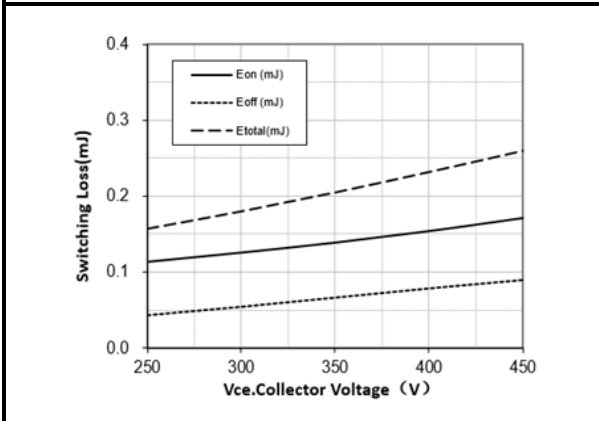


JT05N065RAD/VAD/SAD

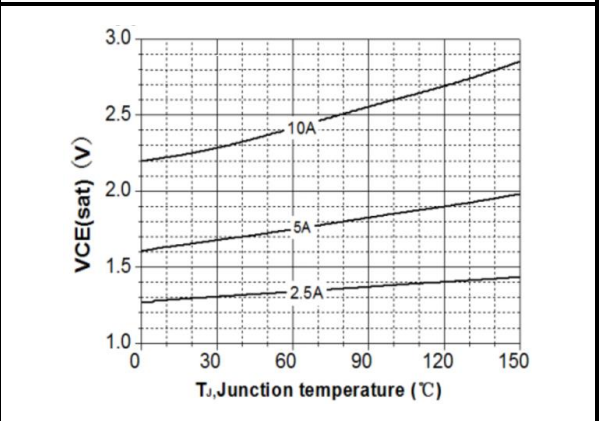




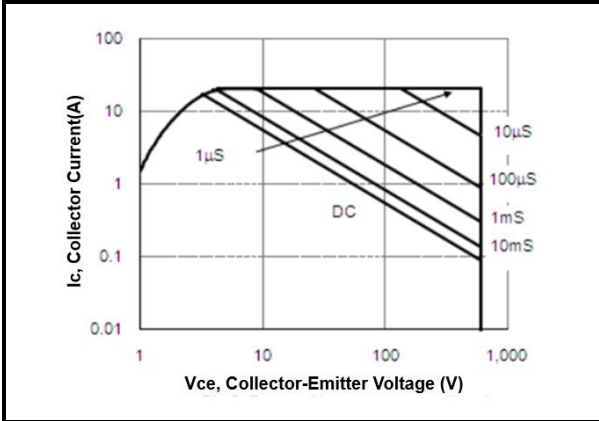
Switching Loss vs Vce
Tj=150°C, Vge=15V, Ic=5A, Rg=60Ω



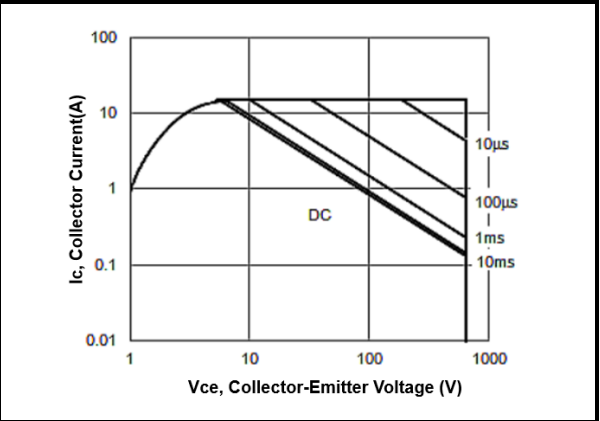
Vcesat vs TJ
Vge = 15V



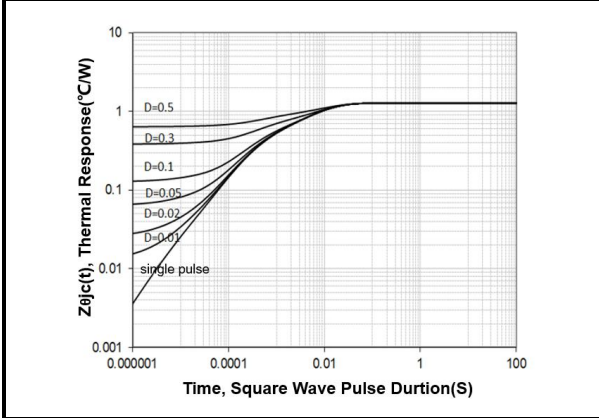
SOA Characteristics For DPAK/IPAK



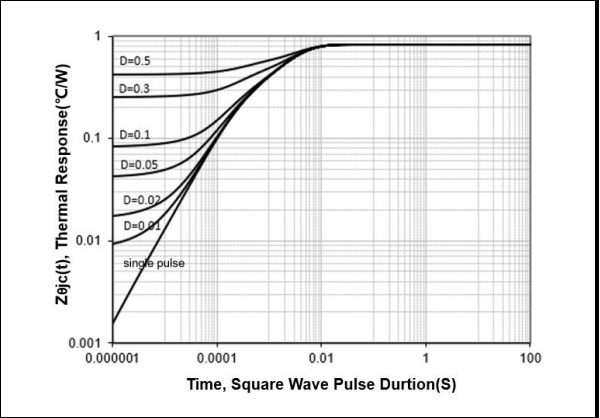
SOA Characteristics For TO-263



Transient Thermal Impedance For DPAK/IPAK(IGBT)



Transient Thermal Impedance For TO-263(IGBT)

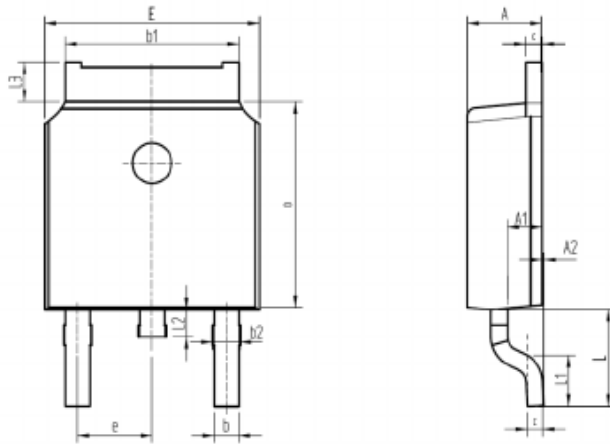




外形尺寸 PACKAGE MECHANICAL DATA

DPAK

单位 Unit: mm

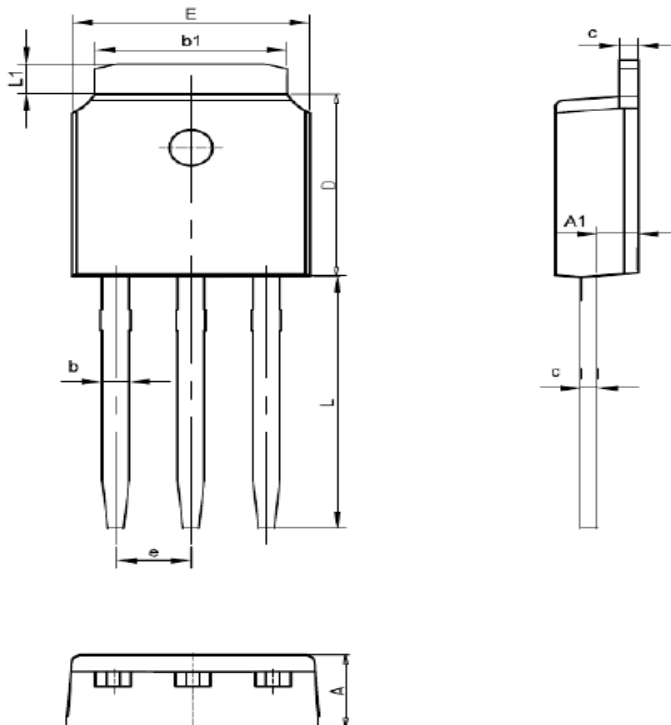


SYMBOL	mm	
	MIN	MAX
A	2.16	2.41
A1	0.97	1.17
A2	0.00	0.15
b	0.63	0.93
b1	5.13	5.53
b2	0.66	0.96
c	0.40	0.60
D	5.80	6.40
E	6.30	6.90
e	2.286BSC	
L	2.50	3.30
L1	1.20	1.80
L2	0.60	1.00
L3	0.85	1.30

外形尺寸 PACKAGE MECHANICAL DATA

IPAK

单位 Unit: mm



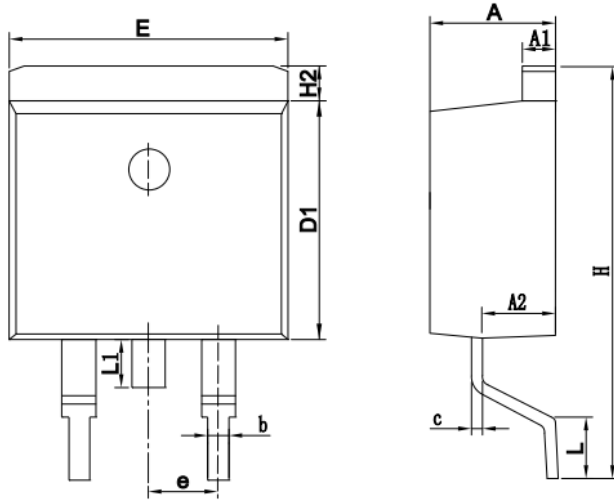
SYMBOL	MM	
	MIN	MAX
A	2.1	2.5
A1	0.87	1.27
b	0.63	0.93
b1	5.13	5.53
c	0.40	0.60
D	5.80	6.40
E	6.30	6.90
L	9.10	9.70
e	2.286BSC	
L1	0.82	1.22



外形尺寸 PACKAGE MECHANICAL DATA

TO-263

单位 Unit: mm



SYMBOL	MM	
	MIN	MAX
A	4.30	4.80
A1	1.12	1.42
A2	2.54	2.84
b	0.67	1.00
c	0.29	0.52
D1	8.40	9.00
E	9.80	10.46
e	2.54BSC	
H	14.00	16.00
H2	1.12	1.45
L	1.50	3.10
L1	1.45	1.70



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